

Features

- Typical Isolation: 35 dB (2.0 GHz)
- Typical Insertion Loss: 1.2 dB (2.0 GHz)
- Integral ASIC/CMOS Driver
- 50 Ohm Nominal Impedance
- Low DC Power Consumption
- Test Boards Available
- Lead-Free QSOP-24 Package
- 100% Matte Tin Plating over Copper
- Halogen-Free “Green” Mold Compound
- 260°C Reflow Compatible
- RoHS* Compliant Version of SW65-0440

Description

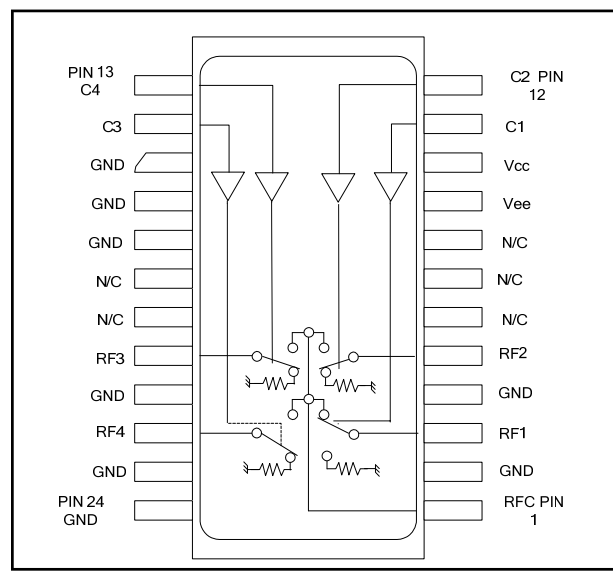
M/A-COM's MASWCC0009 is a GaAs MMIC absorptive SP4T switch with an integral silicon ASIC driver. This device is in a 24-lead plastic package. This switch offers excellent broadband performance and repeatability from DC to 3 GHz, while maintaining low DC power dissipation. The MASWCC0009 is ideally suited for wireless infrastructure applications.

Ordering Information

Part Number	Package
MASWCC0009	Bulk Packaging
MASWCC0009TR	1000 piece reel
MASWCC0009-TB	Sample Test Board

Note: Reference Application Note M513 for reel size information.

Functional Schematic



Pin Configuration

Pin No.	Function	Pin No.	Function
1	RFC	13	C4
2	GND	14	C3
3	RF1	15	GND
4	GND	16	GND
5	RF2	17	GND
6	NC	18	NC
7	NC	19	NC
8	NC	20	RF3
9	V _{EE}	21	GND
10	V _{CC}	22	RF4
11	C1	23	GND
12	C2	24	GND

NC = No Connection

* Restrictions on Hazardous Substances, European Union Directive 2002/95/EC.

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Electrical Specifications: $T_A = 25^\circ\text{C}$

Parameter	Test Conditions	Units	Min	Typ	Max
Insertion Loss	DC - 2.0 GHz	dB	—	1.2	1.8
	DC - 3.0 GHz	dB	—	1.3	2.5
Isolation	DC - 2.0 GHz	dB	32	35	—
	DC - 3.0 GHz	dB	25	29	—
VSWR RF1-RF4 On RF1- RF4 Off RFC RFC	DC - 3.0 GHz	Ratio	—	1.2:1	1.6:1
	DC - 3.0 GHz	Ratio	—	1.4:1	1.8:1
	DC - 2.0 GHz	Ratio	—	1.2:1	1.5:1
	DC - 3.0 GHz	Ratio	—	1.6:1	2.2:1
Switching Speed ¹ T_{rise} T_{fall} T_{on} T_{off} Transients	10%/90%, 90%/10%	ns	—	15	50
	50% TTL to 90%/10% RF	ns	—	50	150
	In-band (peak to peak)	mV	—	50	150
1 dB Compression	.05 GHz	dBm	—	+20	—
	.5 - 3.0 GHz	dBm	—	+27	—
Input IP_3	Two tone inputs 0.05 GHz	dBm	—	+35	—
	up to +5 dBm 0.5 - 3.0 GHz	dBm	—	+46	—
V_{CC}	—	V	+4.5	+5.0	+5.5
V_{EE}	—	V	-8.0	-5.0	-4.75
V_{IL} V_{IH}	LOW-level input voltage	V	0.0	—	0.8
	HIGH-level input voltage	V	2.0	—	5.0
I_{in} (Input Leakage Current)	$V_{in} = V_{CC}$ or GND	uA	-1.0	—	1.0
I_{cc} (Quiescent Supply Current)	$V_{cntrl} = V_{CC}$ or GND	uA	—	250	400
ΔI_{cc} (Additional Supply Current Per TTL Input Pin)	$V_{CC} = \text{Max}$, $V_{cntrl} = V_{CC} - 2.1 \text{ V}$	mA	—	—	1.0
I_{EE}	V_{EE} min to max, $V_{in} = V_{IL}$ or V_{IH}	mA	-1.0	-0.2	—

Absolute Maximum Ratings ^{2,3,4}

1. Decoupling capacitors (0.1 μF) are required on the power supply lines.

Parameter	Absolute Maximum
Max. Input Power 0.05 GHz 0.5 - 3.0 GHz	+27 dBm +34 dBm
V_{CC}	$-0.5\text{V} \leq V_{CC} \leq +7.0\text{V}$
V_{EE}	$-8.5\text{V} \leq V_{EE} \leq +0.5\text{V}$
$V_{CC} - V_{EE}$	$-0.5\text{V} \leq V_{CC} - V_{EE} \leq 14.5\text{V}$
V_{in}^5	$-0.5\text{V} \leq V_{in} \leq V_{CC} + 0.5\text{V}$
Operating Temperature	-40°C to $+85^\circ\text{C}$
Storage Temperature	-65°C to $+125^\circ\text{C}$

- Exceeding any one or combination of these limits may cause permanent damage to this device.
- M/A-COM does not recommend sustained operation near these survivability limits.
- When the RF input is applied to the terminated port, the absolute maximum power is +30 dBm.
- Standard CMOS TTL interface, latch-up will occur if logic signal is applied prior to power supply.

Truth Table (Switch)

TTL				RF Common To:			
C1	C2	C3	C4	RF1	RF2	RF3	RF4
1	0	0	0	On	Off	Off	Off
0	1	0	0	Off	On	Off	Off
0	0	1	0	Off	Off	On	Off
0	0	0	1	Off	Off	Off	On

0 = TTL Low; 1 = TTL High

ADVANCED: Data Sheets contain information regarding a product M/A-COM Technology Solutions is considering for development. Performance is based on target specifications, simulated results, and/or prototype measurements. Commitment to develop is not guaranteed.
PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

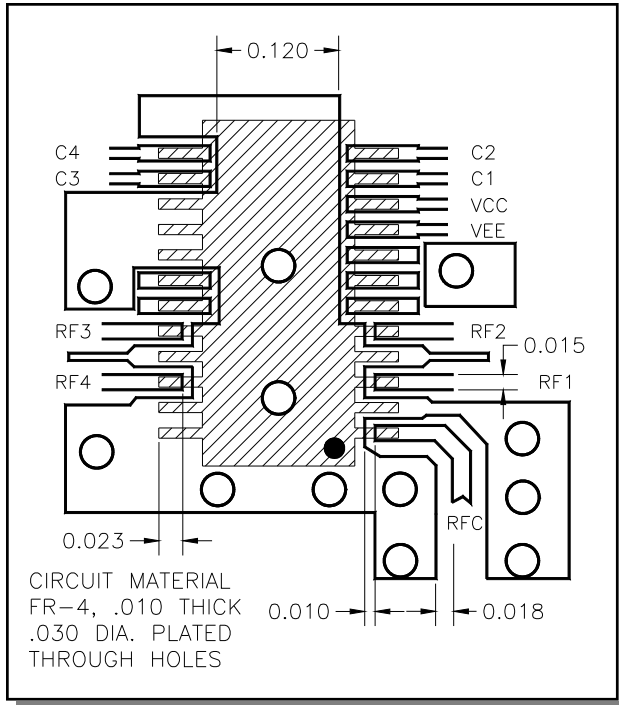
• **North America** Tel: 800.366.2266 • **Europe** Tel: +353.21.244.6400
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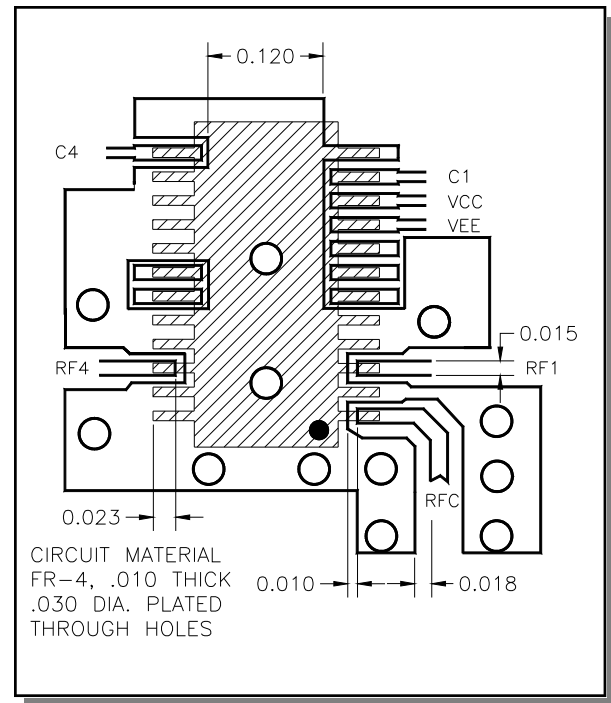
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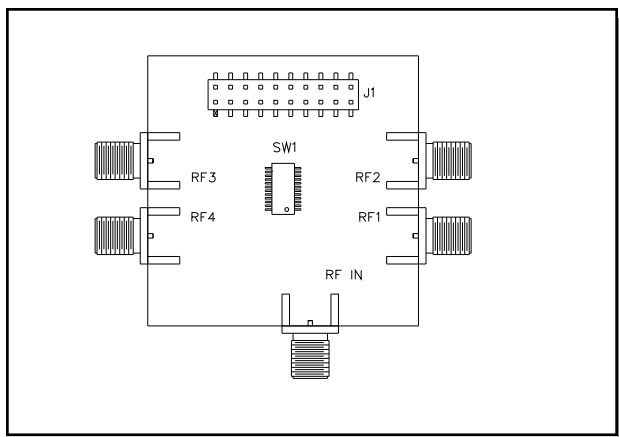
Recommended PCB Layout—SP4T



Recommended PCB Layout—SP2T



Evaluation Board - SW65-0440-TB



Handling Procedures

Please observe the following precautions to avoid damage:

Static Sensitivity

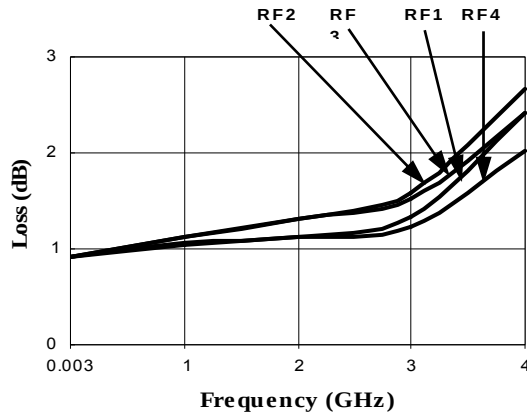
Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

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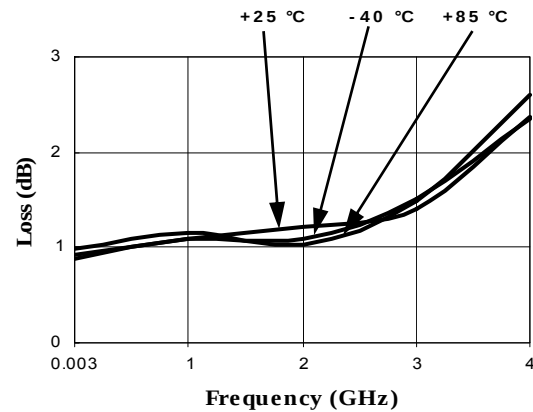
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Typical Performance Curves

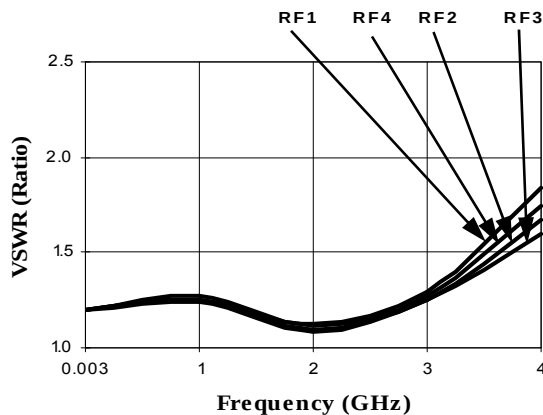
Insertion Loss (dB) @ +25°C



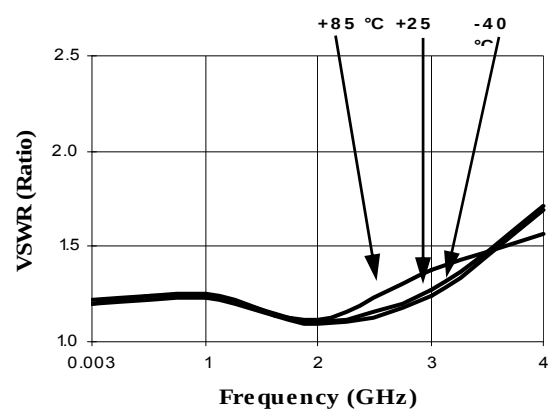
Loss Variation Over Temp. (dB)



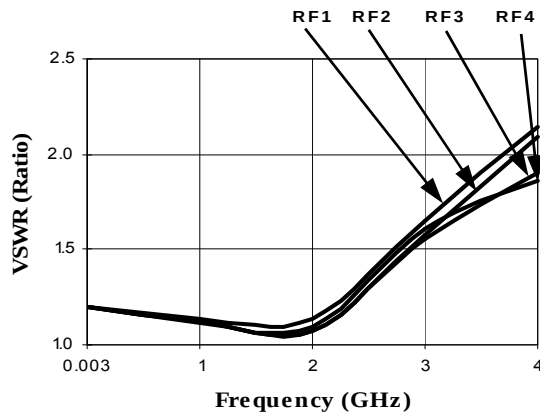
RF1 - RF4 On VSWR @ +25°C



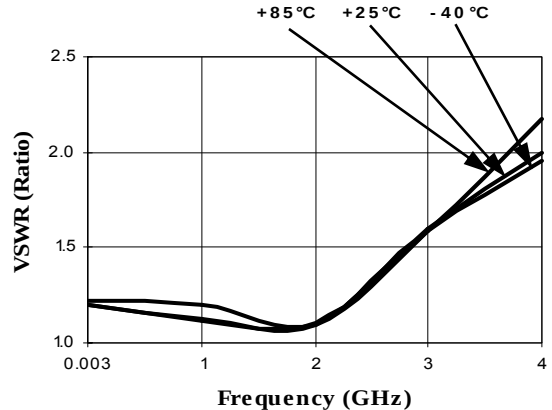
RF1 - RF4 On VSWR Temp. Variation



RFC On VSWR @ +25°C



RFC On VSWR Temp. Variation

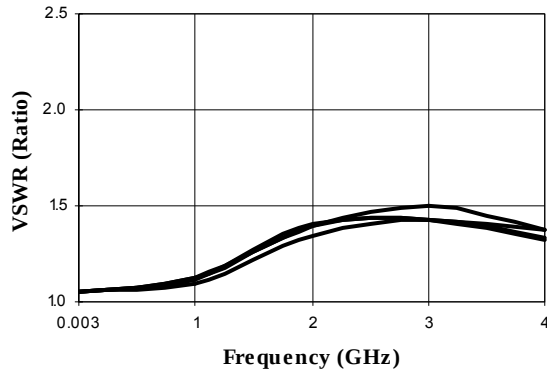


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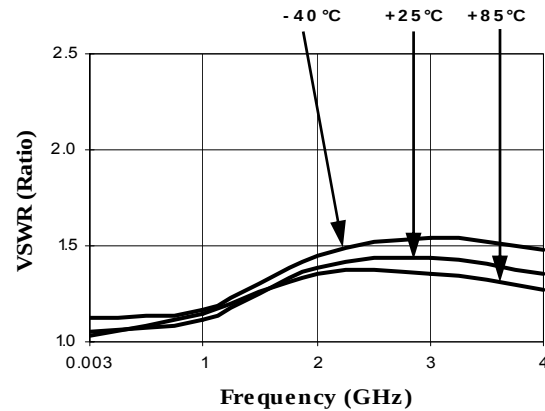
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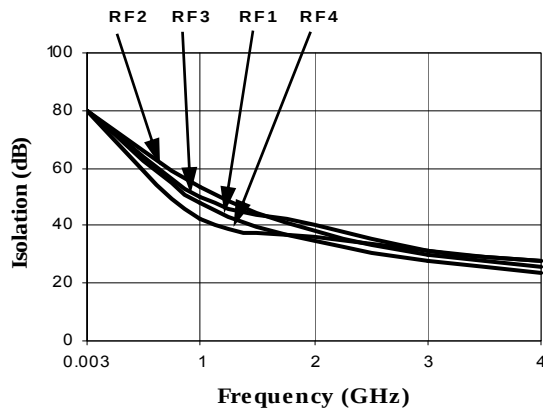
RF1 - RF4 Off VSWR @ +25°C



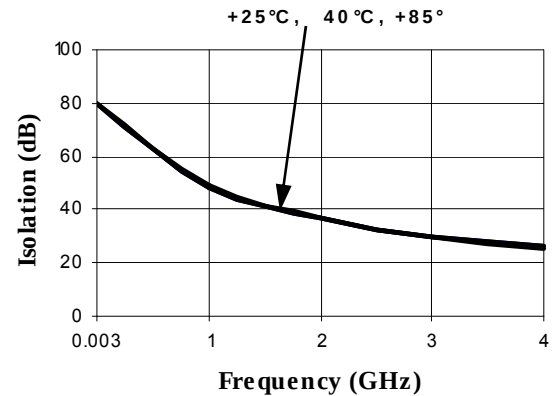
RF1 - RF4 Off VSWR Temp. Variation



Isolation (dB) @ +25°C



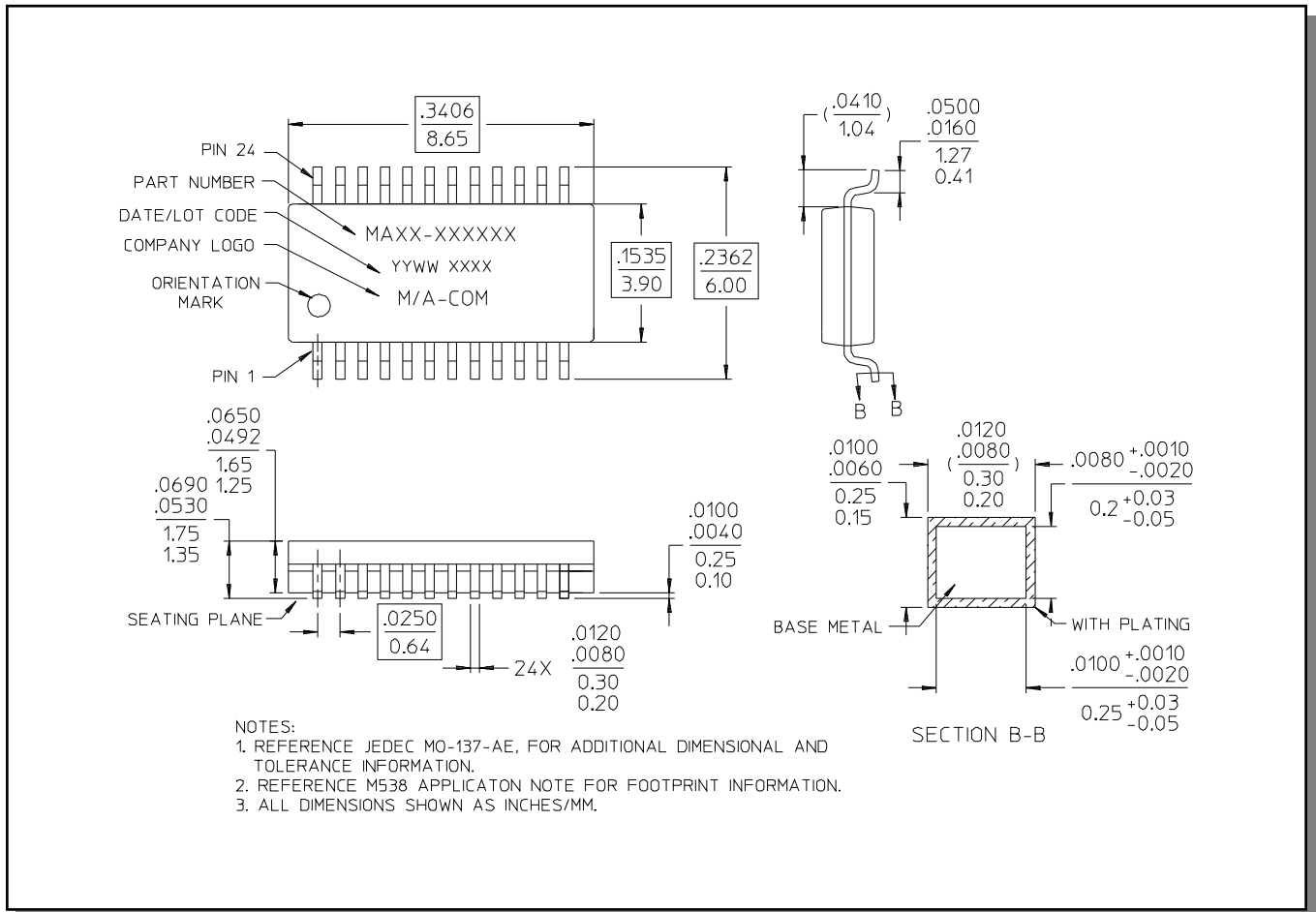
Isolation Temp. Variation (dB)



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Lead-Free, QSOP-24[†]



[†] Reference Application Note M538 for lead-free solder reflow recommendations.